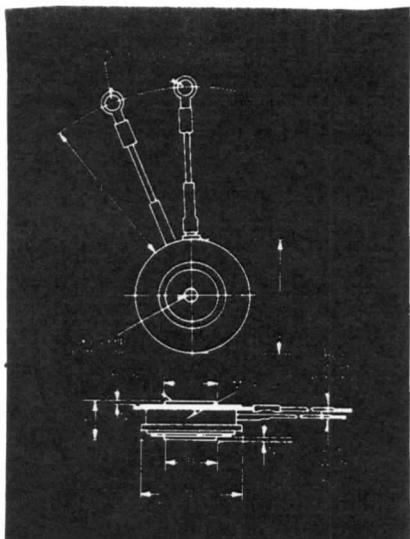


New Jersey Semi-Conductor Products, Inc.

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T62 Outline

Features:

- Center fired di/namic gate
- High di/dt with soft gate control
- High frequency operation
- Sinusoidal waveform operation to 20 KHz
- Rectangular waveform operation to 20 KHz
- Low dynamic forward voltage drop
- Low switching losses at high frequency

Applications:

- Inverters for
Ups
Induction Heating
Motor Control
- Choppers
- Crowbars

Symbol	Inches		Millimeters	
	Min.	Max.	Min.	Max.
ϕD	1.610	1.650	40.89	41.91
ϕD_1	.745	.755	18.92	19.18
ϕD_2	1.420	1.460	36.07	37.08
H	.500	.560	12.70	14.22
ϕJ	.135	.145	3.43	3.68
J_1	.072	.082	1.83	2.08
L	7.75	8.50	196.85	215.90
N	.030		.76	

Creep Distance—.34 in. min. (8.64 mm).

Strike Distance—.26 in. min. (6.60 mm).

(In accordance with NEMA standards.)

Finish—Nickel Plate.

Approx. Weight—2.3 oz. (66 g).

1. Dimension "H" is clamped dimension.

T627 SERIES
SCR FAST SWITCHING
150A Avg up to 1200 Volts

Ordering Information

Type	Voltage	Current	Turn-off	Gate Current	Leads
	V_{DRM} and V_{RRM} (V)	$I_{T(av)}$ (A)	t_q μsec	I_{GT} (ma)	Case
T627	100	150	10	150	T62
	200		15		
	300		20		
	400		30		
	500		40		
	600		50		
	700				
	800				
	900				
	1000				
	1100				
	1200				

Example

Obtain optimum device performance for your application by selecting proper Order Code.

Type T627 rated at 150A average with $V_{DRM} = 1000V$,
 $I_{GT} = 150 ma$, $t_q = 20 \mu sec$ max. and flex leads—order as:

Type	Voltage	Current	Turn Off	Gate Current	Leads
T 6 2 7	1 0	1 5	6	4	D N

*for 10 μsec turn-off.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Voltage

Blocking State Maximums ^① ($T_J = 125^\circ\text{C}$)

Repetitive peak forward blocking voltage, V ...
 Repetitive peak reverse voltage, V ...
 Non-repetitive transient peak reverse voltage,
 $t \leq 5.0 \text{ msec}$, V ...

Symbol

V_{DRM}
 V_{RRM}
 V_{RSM}

100	200	300	400	500	600	700	800	900	1000	1100	1200
100	200	300	400	500	600	700	800	900	1000	1100	1200
200	300	400	500	600	700	800	900	1000	1100	1200	1300

Forward leakage current, mA peak ...
 Reverse leakage current, mA peak ...

I_{DRM}
 I_{RRM}

25	25
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Current

Conducting State Maximums ($T_J = 125^\circ\text{C}$)

Symbol

T627-15

RMS forward current, A ...
 Ave. forward current, A ...
 One-half cycle surge current^③, A ...
 I^2t for fusing (for times $\geq 8.3 \text{ ms}$)
 $A^2 \text{ sec}$...
 Forward voltage drop at $I_{TM} = 625 \text{ A}$
 and $T_J = 25^\circ\text{C}$, V ...
 Min. repetitive di/dt ^④, A/ μsec ^{①②④}

$I_{T(rms)}$
 $I_{T(av)}$
 I_{TSM}
 I^2t
 V_{TM}
 di/dt

235
 150
 3500
 50,000
 2.35
 200

Switching

($T_J = 25^\circ\text{C}$)

Symbol

Max. turn-off time, $I_T = 150 \text{ A}$,
 $T_J = 125^\circ\text{C}$, $di/dt = 12.5$ ^①
 $A/\mu\text{sec}$, reappplied $dv/dt =$
 $20 \text{ V}/\mu\text{sec}$ ^④ linear to $0.8 V_{DRM}$, μsec ...
 Typ. turn-on time, $I_T = 100 \text{ A}$
 $V_D = 100 \text{ V}$ ^④, μsec ...
 Min. critical dv/dt , exponential to V_{DRM} ,
 $T_J = 125^\circ\text{C}$, $V/\mu\text{sec}$ ^{②④} ...
 Min. di/dt A/ μsec ^{①④④}

t_q
 t_{on}
 dv/dt
 di/dt

10 to 50
 3.5
 300
 800

Gate

Maximum Parameters ($T_J = 25^\circ\text{C}$)

Symbol

Gate current to trigger at $V_D = 12 \text{ V}$, mA ...
 Gate voltage to trigger at $V_D = 12 \text{ V}$, V ...
 Non-triggering gate voltage, $T_J = 125^\circ\text{C}$,
 and rated V_{DRM} , V ...
 Peak forward gate current, A ...
 Peak reverse gate voltage, V ...
 Peak gate power, Watts ...
 Average gate power, Watts ...

I_{GT}
 V_{GT}
 V_{GDM}
 I_{GTM}
 V_{GRM}
 P_{GM}
 $P_{G(av)}$

150
 3
 0.15
 4
 5
 16
 3

Thermal and Mechanical

Symbol

Min., Max. oper. junction temp., $^\circ\text{C}$...
 Min., Max. storage temp., $^\circ\text{C}$...
 Min., Max. Mounting Force, lb. ^① ...
 Max. thermal resistance, Double side cooled
 Junction to case, $^\circ\text{C}/\text{Watt}$...
 Case to sink, lubricated, $^\circ\text{C}/\text{Watt}$...

T_J
 T_{stg}
 $R_{\theta JC}$
 $R_{\theta CS}$

-40 to +125
 -40 to +150
 1000 to 1400
 .08
 .02

- ① Consult recommended mounting procedures.
- ② Applies for zero or negative gate bias.
- ③ Per JEDEC RS-397, 5.2.2.1.
- ④ With recommended gate drive.
- ⑤ Higher dv/dt ratings available, consult factory.
- ⑥ Per JEDEC standard RS-397, 5.2.2.6.
- ⑦ For operation with antiparallel diode, consult factory.

